HALOGEN FREE

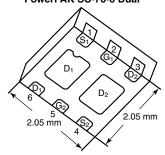




Dual N-Channel 12 V (D-S) MOSFET

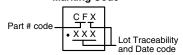
PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a	Q _g (Typ.)						
12	0.028 at V _{GS} = 4.5 V	4.5							
	0.033 at V _{GS} = 2.5 V	4.5	6.2 nC						
	0.042 at Vgs = 1.8 V	4.5							

PowerPAK SC-70-6 Dual



Ordering Information: SiA910EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

Marking Code

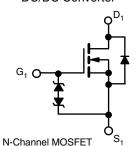


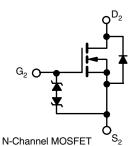
FEATURES

- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection: 2400 V
- 100 % R_a Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Load Switch for Portable Applications
- High Frequency DC/DC Converter
- DC/DC Converter





Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	12	V	
Gate-Source Voltage		V _{GS}	± 8		
	$T_C = 25 ^{\circ}C$ $T_C = 70 ^{\circ}C$		4.5 ^a 4.5 ^a		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	4.5 ^{a, b, c}		
Pulsed Drain Current	T _A = 70 °C	I _{DM}	4.5 ^{a, b, c}	Α	
	T _C = 25 °C	·DIVI	4.5 ^a		
Continuous Source-Drain Diode Current	T _A = 25 °C	Is	1.6 ^{b, c}		
	T _C = 25 °C		7.8		
Maximum Power Dissipation	T _C = 70 °C	P _D	5	w	
Maximum Fower Dissipation	T _A = 25 °C	υ υ	1.9 ^{b, c}	**	
	T _A = 70 °C		1.2 ^{b, c}		
Operating Junction and Storage Temperatur	e Range	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature	ature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS										
Parameter		Symbol	Typical	Maximum	Unit					
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	52	65	°C/W					
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	12.5	16	C/ VV					

Notes:

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 110 °C/W.

Document Number: 65535 S13-0460-Rev. B, 04-Mar-13 For technical questions, contact: pmostechsupport@vishav.com



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	-				l	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	12			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 250 A		8		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 2.5		mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_{D} = 250 \mu A$	0.4		1	V
Oata Oassaa Laalaasa	,	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 5	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 0.5	μΑ
Zone Ooto Voltana Dunia Orumant		V _{DS} = 12 V, V _{GS} = 0 V			1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			Α
		$V_{GS} = 4.5 \text{ V}, I_D = 5.2 \text{ A}$		0.023	0.028	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 4.8 A		0.027	0.033	Ω
		V _{GS} = 1.8 V, I _D = 2.5 A		0.035	0.042	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 5.2 A		23		S
Dynamic ^b						l
Input Capacitance	C _{iss}			455		pF
Output Capacitance	C _{oss}	V _{DS} = 6 V, V _{GS} = 0 V, f = 1 MHz		190		
Reverse Transfer Capacitance	C _{rss}			150		
Total Oats Observe	0	V _{DS} = 6 V, V _{GS} = 8 V, I _D = 6.8 A		10.5	16	
Total Gate Charge	Q_g			6.2	9.5	nC
Gate-Source Charge	Q _{gs}	$V_{DS} = 6 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.8 \text{ A}$		0.8		
Gate-Drain Charge	Q _{gd}			1.6		
Gate Resistance	R_g	f = 1 MHz	0.8	4	8	Ω
Turn-On Delay Time	t _{d(on)}			10	15	
Rise Time	t _r	$V_{DD} = 6 \text{ V}, R_{I} = 1.1 \Omega$		12	20	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 5.4 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_q = 1 \Omega$		25	40	
Fall Time	t _f	D = 0.171, *GEN = 1.0 *, 1.g = 1.22		12	20	
Turn-On Delay Time	t _{d(on)}			5	10	ns
Rise Time	t _r	$V_{DD} = 6 \text{ V}, R_{L} = 1.1 \Omega$		10	15	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 5.4 \text{ A}, V_{GEN} = 10 \text{ V}, R_a = 1 \Omega$		20	30	
Fall Time	t _f	D = 0.174, *GEN = 10 *, 1 * * * * * * * * * * * * * * * * *		10	15	
Drain-Source Body Diode Characteristic	s					,
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			4.5	Α
Pulse Diode Forward Current	I _{SM}				20	
Body Diode Voltage V _{SD}		$I_S = 5.4 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time t _{rr}				25	50	ns
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 5.4 A, dI/dt = 100 A/μs, T _J = 25 °C		10	20	nC
Reverse Recovery Fall Time	t _a	1; - 3.7 Λ, αι/αι - 100 Λ/μ3, 1j - 23 · 0		13		ns
Reverse Recovery Rise Time	t _b			12		115

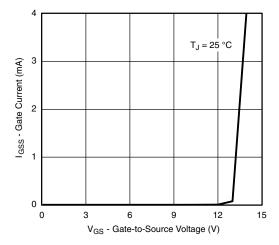
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing.

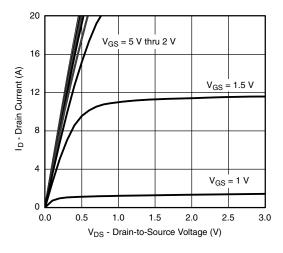
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



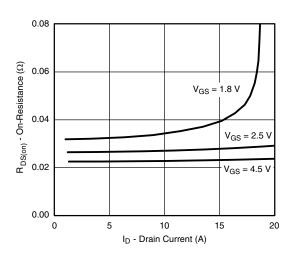
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



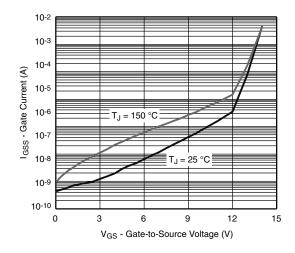
Gate Current vs. Gate-Source Voltage



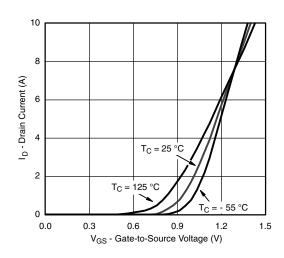
Output Characteristics



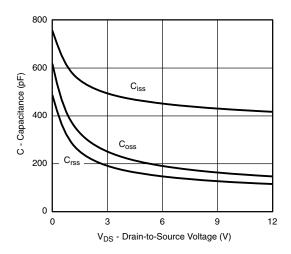
On-Resistance vs. Drain Current and Gate Voltage



Gate Current vs. Gate-Source Voltage

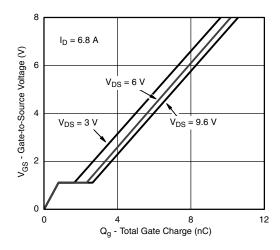


Transfer Characteristics

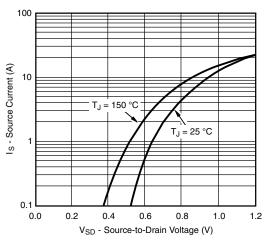


Capacitance

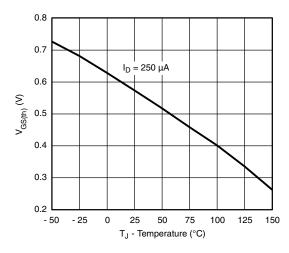
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



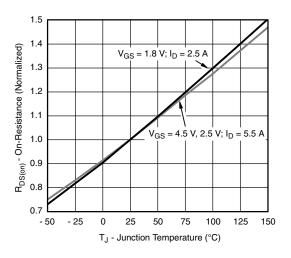
Gate Charge



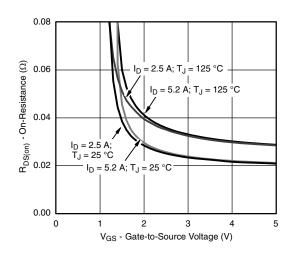
Source-Drain Diode Forward Voltage



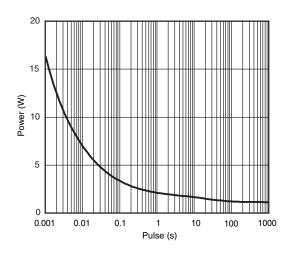
Threshold Voltage



On-Resistance vs. Junction Temperature



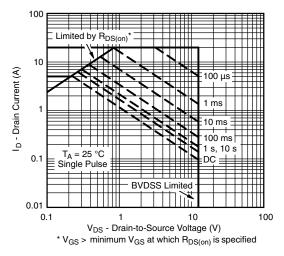
On-Resistance vs. Gate-to-Source Voltage



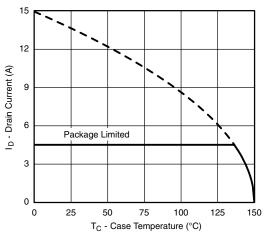
Single Pulse Power (Junction-to-Ambient)

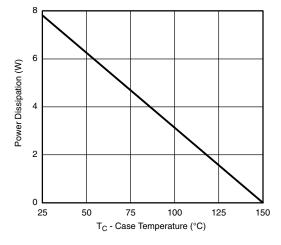


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient





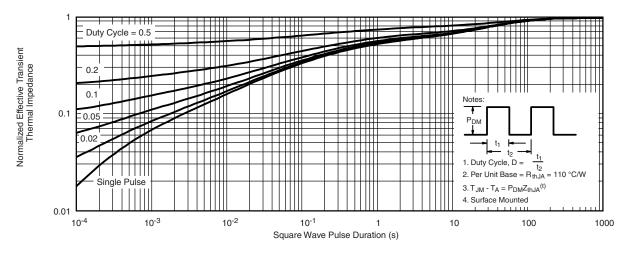
Current Derating*

Power Derating

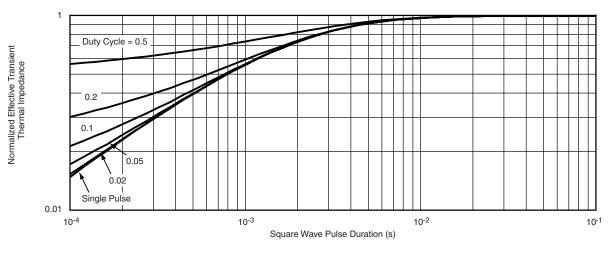
^{*} The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppq?65535.





PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

			SINGL	E PAD			DUAL PAD					
DIM	M	ILLIMETER	RS		INCHES		M	ILLIMETER	RS		INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	,	0.65 BSC			0.026 BSC		
K		0.275 TYP	1		0.011 TYP		0.275 TYP 0.011 TYP					
K1	0.400 TYP 0.016 TYP				0.320 TYP			0.013 TYP				
K2	0.240 TYP 0.009 TYP			0.252 TYP			0.010 TYP					
К3		0.225 TYP	TYP 0.009 TYP									
K4	0.355 TYP 0.014 TYP											
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
ECNI- C C	7404 D	. 0 00 1	. 07									

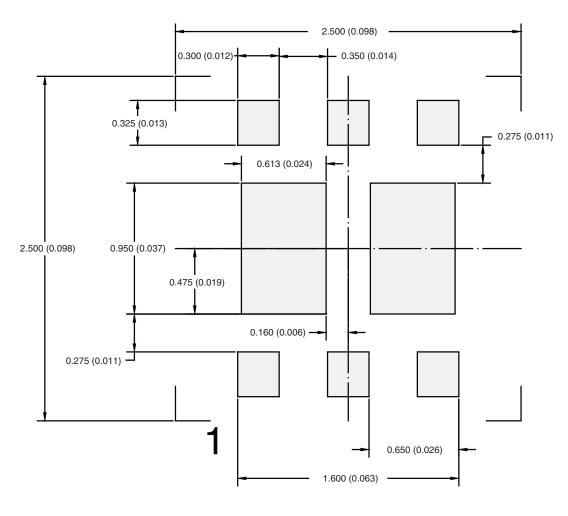
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

Return to Index



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.